

August 2001

## Ultra Low Noise, Precision Operational Amplifier

### Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- High Slew Rate . . . . . 7V/μs (Min)
- Unity Gain Bandwidth . . . . . 5MHz (Min)
- Low Noise Voltage (at 1kHz) . . . . . 4.5nV/√Hz (Max)
- Low Offset Voltage . . . . . 100μV (Max)
- Low Offset Drift With Temperature . . . . . 1.8μV/°C (Max)
- High CMRR . . . . . 100dB (Min)
- High Voltage Gain . . . . . 700kV/V (Min)

### Applications

- High Speed Signal Conditioners
- Wide Bandwidth Instrumentation Amplifiers
- Low Level Transducer Amplifiers
- Fast, Low Level Voltage Comparators
- Highest Quality Audio Preamplifiers
- Pulse/RF Amplifiers

### Description

The HA-5127/883 monolithic operational amplifier features an excellent combination of precision DC and wideband high speed characteristics. Utilizing the Intersil D.I. technology and advanced processing techniques, this unique design unites low noise precision instrumentation performance with high speed, wideband capability.

This amplifier's impressive list of features include low  $V_{OS}$ , wide gain-bandwidth, high open loop gain, and high CMRR. Additionally, this flexible device operates over a wide supply range while consuming only 120mW of power.

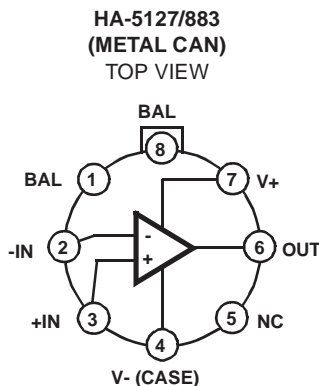
Using the HA-5127/883 allows designers to minimize errors while maximizing speed and bandwidth.

This device is ideally suited for low level transducer signal amplifier circuits. Other applications which can utilize the HA-5127/883's qualities include instrumentation amplifiers, pulse or RF amplifiers, audio preamplifiers, and signal conditioning circuits.

### Ordering Information

PART NUMBER	TEMPERATURE RANGE	PACKAGE
HA2-5127/883	-55°C to +125°C	8 Pin Can

### Pinout



## Specifications HA-5127/883

## Absolute Maximum Ratings

Voltage Between V+ and V- Terminals	44V
Differential Input Voltage (Note 2)	0.7V
Voltage at Either Input Terminal	V+ to V-
Input Current	±25mA
Differential Output Current	Full Short Circuit Protection
Junction Temperature (T <sub>J</sub> )	+175°C
Storage Temperature Range	-65°C to +150°C
ESD Rating	<2000V
Lead Temperature (Soldering 10s)	+300°C

## Thermal Information

Thermal Resistance	$\theta_{JA}$	$\theta_{JC}$
Metal Can Package	155°C/W	67°C/W
Package Power Dissipation Limit at +75°C for T <sub>J</sub> ≤ +175°C		
Metal Can Package		645mW
Package Power Dissipation Derating Factor Above +75°C		
Metal Can Package		6.5mW/°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

## Recommended Operating Conditions

Operating Temperature Range	-55°C to +125°C	$V_{INCM} \leq 1/2 (V+ - V-)$
Operating Supply Voltage	±15V	$R_L \geq 600\Omega$

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: V<sub>SUPPLY</sub> = ±15V, R<sub>SOURCE</sub> = 50Ω, R<sub>LOAD</sub> = 100kΩ, V<sub>OUT</sub> = 0V, Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Input Offset Voltage	V <sub>IO</sub>	V <sub>CM</sub> = 0V	1	+25°C	-100	100	μV
			2, 3	+125°C, -55°C	-300	300	μV
Input Bias Current	I <sub>B</sub>	V <sub>CM</sub> = 0V, R <sub>S</sub> = 10kΩ, 50Ω $\left( \frac{ I_{B+}  +  I_{B-} }{2} \right)$	1	+25°C	-	80	nA
			2, 3	+125°C, -55°C	-	150	nA
Input Offset Current	I <sub>IO</sub>	V <sub>CM</sub> = 0V, +R <sub>S</sub> = 10kΩ, -R <sub>S</sub> = 10kΩ	1	+25°C	-75	75	nA
			2, 3	+125°C, -55°C	-135	135	nA
Common Mode Range	+CMR	V+ = +4.7V, V- = -25.3V	1	+25°C	10.3	-	V
			2, 3	+125°C, -55°C	10.3	-	V
	-CMR	V+ = +25.3V, V- = -4.7V	1	+25°C	-	-10.3	V
			2, 3	+125°C, -55°C	-	-10.3	V
Large Signal Voltage Gain	+A <sub>VOL</sub>	V <sub>OUT</sub> = 0V and +10V, R <sub>L</sub> = 2kΩ	4	+25°C	700	-	kV/V
			5, 6	+125°C, -55°C	300	-	kV/V
	-A <sub>VOL</sub>	V <sub>OUT</sub> = 0V and -10V, R <sub>L</sub> = 2kΩ	4	+25°C	700	-	kV/V
			5, 6	+125°C, -55°C	300	-	kV/V
Common Mode Rejection Ratio	+CMRR	ΔV <sub>CM</sub> = +11V	1	+25°C	100	-	dB
		ΔV <sub>CM</sub> = +10V	2, 3	+125°C, -55°C	100	-	dB
	-CMRR	ΔV <sub>CM</sub> = -11V	1	+25°C	100	-	dB
		ΔV <sub>CM</sub> = -10V	2, 3	+125°C, -55°C	100	-	dB
Output Voltage Swing	+V <sub>OUT1</sub>	R <sub>L</sub> = 2kΩ	4	+25°C	11.5	-	V
			5, 6	+125°C, -55°C	11.5	-	V
	-V <sub>OUT1</sub>	R <sub>L</sub> = 2kΩ	4	+25°C	-	-11.5	V
			5, 6	+125°C, -55°C	-	-11.5	V
	+V <sub>OUT2</sub>	R <sub>L</sub> = 600Ω	4	+25°C	10	-	V
			4	+25°C	-	-10	V

## Specifications HA-5127/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at:  $V_{SUPPLY} = \pm 15V$ ,  $R_{SOURCE} = 50\Omega$ ,  $R_{LOAD} = 100k\Omega$ ,  $V_{OUT} = 0V$ , Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUPS	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Output Current	+I <sub>OUT</sub>	V <sub>OUT</sub> = -10V	4	+25°C	16.5	-	mA
	-I <sub>OUT</sub>	V <sub>OUT</sub> = +10V	4	+25°C	-	-16.5	mA
Quiescent Power Supply Current	+I <sub>CC</sub>	V <sub>OUT</sub> = 0V, I <sub>OUT</sub> = 0mA	1	+25°C	-	4	mA
			2, 3	+125°C, -55°C	-	4	mA
	-I <sub>CC</sub>	V <sub>OUT</sub> = 0V, I <sub>OUT</sub> = 0mA	1	+25°C	-4	-	mA
			2, 3	+125°C, -55°C	-4	-	mA
Power Supply Rejection Ratio	+PSRR	$\Delta V_{SUP} = 14V$	1	+25°C	86	-	dB
		$\Delta V_{SUP} = 13.5V$	2, 3	+125°C, -55°C	86	-	dB
	-PSRR	$\Delta V_{SUP} = 14V$	1	+25°C	86	-	dB
		$\Delta V_{SUP} = 13.5V$	2, 3	+125°C, -55°C	86	-	dB
Offset Voltage Adjustment	+V <sub>IOAdj</sub>	Note 1	1	+25°C	V <sub>IO</sub> -1	-	mV
			2, 3	+125°C, -55°C	V <sub>IO</sub> -1	-	mV
	-V <sub>IOAdj</sub>	Note 1	1	+25°C	V <sub>IO</sub> +1	-	mV
			2, 3	+125°C, -55°C	V <sub>IO</sub> +1	-	mV

NOTE:

- Offset adjustment range is [V<sub>IO</sub> (Measured) ±1mV] minimum referred to output. This test is for functionality only to assure adjustment through 0V.
- For differential input voltages greater than 0.7V, the input current must be limited to 25mA to protect the back-to-back input diodes.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at:  $V_{SUPPLY} = \pm 15V$ ,  $R_{SOURCE} = 50\Omega$ ,  $R_{LOAD} = 2k\Omega$ ,  $C_{LOAD} = 50pF$ ,  $A_{VCL} = +1V/V$ , Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	GROUP A SUBGROUP	TEMPERATURE	LIMITS		UNITS
					MIN	MAX	
Slew Rate	+SR	V <sub>OUT</sub> = -3V to +3V	7	+25°C	7	-	V/μs
	-SR	V <sub>OUT</sub> = +3V to -3V	7	+25°C	7	-	V/μs
Rise and Fall Time	t <sub>R</sub>	V <sub>OUT</sub> = 0 to +200mV 10% ≤ T <sub>R</sub> ≤ 90%	7	+25°C	-	150	ns
	t <sub>F</sub>	V <sub>OUT</sub> = 0 to -200mV 10% ≤ T <sub>F</sub> ≤ 90%	7	+25°C	-	150	ns
Overshoot	+OS	V <sub>OUT</sub> = 0 to +200mV	7	+25°C	-	40	%
	-OS	V <sub>OUT</sub> = 0 to -200mV	7	+25°C	-	40	%

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at:  $V_{SUPPLY} = \pm 15V$ ,  $R_{LOAD} = 2k\Omega$ ,  $C_{LOAD} = 50pF$ ,  $A_V = +1V/V$ , Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		
					MIN	MAX	UNITS
Average Offset Voltage Drift	V <sub>IO</sub> TC	V <sub>CM</sub> = 0V	1	-55°C to +125°C	-	1.8	μV/°C
Differential Input Resistance	R <sub>IN</sub>	V <sub>CM</sub> = 0V	1	+25°C	0.8	-	MΩ

## Specifications HA-5127/883

### TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Characterized at:  $V_{SUPPLY} = \pm 15V$ ,  $R_{LOAD} = 2k\Omega$ ,  $C_{LOAD} = 50pF$ ,  $A_V = +1V/V$ , Unless Otherwise Specified.

PARAMETERS	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	LIMITS		
					MIN	MAX	UNITS
Low Frequency Peak-to-Peak Noise	$E_{NP-P}$	0.1Hz to 10Hz	1	+25°C	-	0.25	$\mu V_{P-P}$
Input Noise Voltage Density	$E_N$	$R_S = 20\Omega$ , $f_O = 10Hz$	1	+25°C	-	10.0	$nV/\sqrt{Hz}$
		$R_S = 20\Omega$ , $f_O = 100Hz$	1	+25°C	-	5.6	$nV/\sqrt{Hz}$
		$R_S = 20\Omega$ , $f_O = 1kHz$	1	+25°C	-	4.5	$nV/\sqrt{Hz}$
Input Noise Current Density	$I_N$	$R_S = 2M\Omega$ , $f_O = 10Hz$	1	+25°C	-	4.0	$pA/\sqrt{Hz}$
		$R_S = 2M\Omega$ , $f_O = 100Hz$	1	+25°C	-	2.3	$pA/\sqrt{Hz}$
		$R_S = 2M\Omega$ , $f_O = 1kHz$	1	+25°C	-	0.6	$pA/\sqrt{Hz}$
Unity Gain Bandwidth	UGBW	$V_O = 100mV$	1	+25°C	5	-	MHz
Full Power Bandwidth	FPBW	$V_{PEAK} = 10V$	1, 2	+25°C	111	-	kHz
Minimum Closed Loop Stable Gain	CLSG	$R_L = 2k\Omega$ , $C_L = 50pF$	1	-55°C to +125°C	$\pm 1$	-	V/V
Settling Time	$t_S$	To 0.1% for a 10V Step	1	+25°C	-	2	$\mu s$
Output Resistance	$R_{OUT}$	Open Loop	1	+25°C	-	100	$\Omega$
Quiescent Power Consumption	PC	$V_{OUT} = 0V$ , $I_{OUT} = 0mA$	1, 3	-55°C to +125°C	-	120	mW

#### NOTES:

- Parameters listed in Table 3 are controlled via design or process parameters and are not directly tested at final production. These parameters are lab characterized upon initial design release, or upon design changes. These parameters are guaranteed by characterization based upon data from multiple production runs which reflect lot to lot and within lot variation.
- Full Power Bandwidth guarantee based on Slew Rate measurement using  $FPBW = \text{Slew Rate}/(2\pi V_{PEAK})$ .
- Quiescent Power Consumption based upon Quiescent Supply Current test maximum. (No load on output.)

### TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLES 1 AND 2) (NOTE 2)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1 (Note 1), 2, 3, 4, 5, 6, 7
Group A Test Requirements	1, 2, 3, 4, 5, 6, 7
Groups C and D Endpoints	1

#### NOTES:

- PDA applies to Subgroup 1 only.
- The Subgroup assignments of the parameters in these tables were patterned after Mil-M-38510/135, with the exception of  $V_{IO}$ , which is Subgroups 1, 2, 3.

## Die Characteristics

### DIE DIMENSIONS:

104 x 65 x 19 mils  $\pm$  1 mils

2650 x 1650 x 483 $\mu$ m  $\pm$  25.4 $\mu$ m

### METALLIZATION:

Type: Al, 1% Cu

Thickness: 16k $\text{\AA}$   $\pm$  2k $\text{\AA}$

### GLASSIVATION:

Type: Nitride (Si<sub>3</sub>N<sub>4</sub>) over Silox (SiO<sub>2</sub>, 5% Phos.)

Silox Thickness: 12k $\text{\AA}$   $\pm$  2k $\text{\AA}$

Nitride Thickness: 3.5k $\text{\AA}$   $\pm$  1.5k $\text{\AA}$

### WORST CASE CURRENT DENSITY:

$3.6 \times 10^5 \text{A/cm}^2$

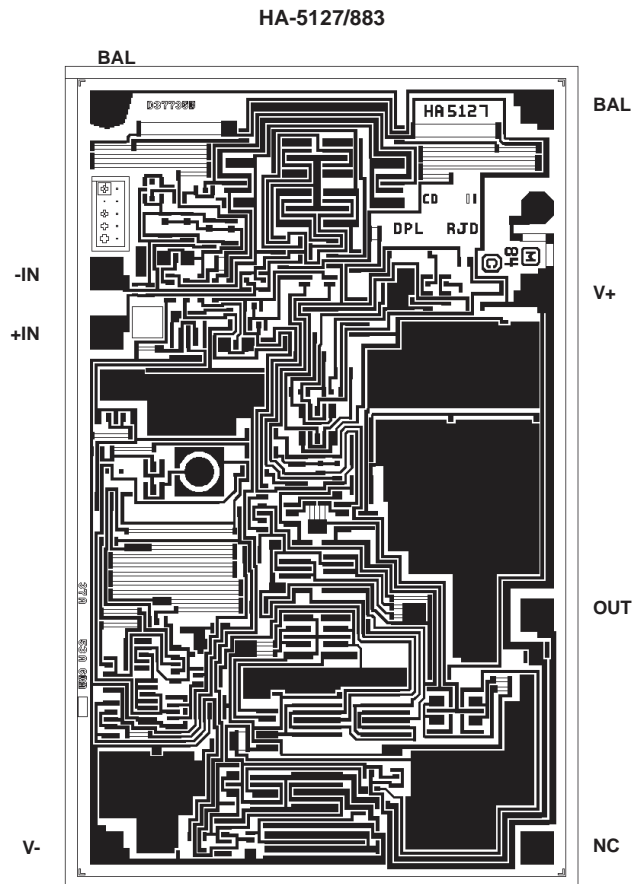
This device meets Glassivation Integrity Test Requirement per MIL-STD-883 Method 2021 and MIL-I-38535 Paragraph 30.5.5.4.

**SUBSTRATE POTENTIAL (Powered Up):** V-

**TRANSISTOR COUNT:** 63

**PROCESS:** Bipolar Dielectric Isolation

## Metallization Mask Layout



All Intersil products are manufactured, assembled and tested utilizing ISO9000 quality systems.  
Intersil Corporation's quality certifications can be viewed at [www.intersil.com/design/quality](http://www.intersil.com/design/quality)

*Intersil products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.*

For information regarding Intersil Corporation and its products, see [www.intersil.com](http://www.intersil.com)

### **Sales Office Headquarters**

#### **NORTH AMERICA**

Intersil Corporation  
7585 Irvine Center Drive  
Suite 100  
Irvine, CA 92618  
TEL: (949) 341-7000  
FAX: (949) 341-7123

Intersil Corporation  
2401 Palm Bay Rd.  
Palm Bay, FL 32905  
TEL: (321) 724-7000  
FAX: (321) 724-7946

#### **EUROPE**

Intersil Europe Sarl  
Ave. C - F Ramuz 43  
CH-1009 Pully  
Switzerland  
TEL: +41 21 7293637  
FAX: +41 21 7293684

#### **ASIA**

Intersil Corporation  
Unit 1804 18/F Guangdong Water Building  
83 Austin Road  
TST, Kowloon Hong Kong  
TEL: +852 2723 6339  
FAX: +852 2730 1433